

The RF Line

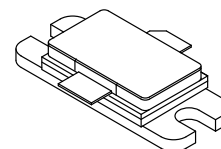
Microwave Pulse Power Transistor

Designed for 1025–1150 MHz pulse common base amplifier applications such as TCAS, T ACAN and Mode-S transmitters.

- Guaranteed Performance @ 1090 MHz
Output Power = 500 Watts Peak
Gain = 8.5 dB Min, 9.0 dB (Typ)
- 100% Tested for Load Mismatch at All Phase Angles with 10:1 VSWR
- Hermetically Sealed Industry Package
- Silicon Nitride Passivated
- Gold Metallized, Emitter Ballasted for Long Life and Resistance to Metal Migration
- Internal Input and Output Matching
- Characterized with 10 μ s, 1% Duty Cycle Pulses

MRF10502

**500 W (PEAK)
1025–1150 MHz
MICROWAVE POWER
TRANSISTOR
NPN SILICON**



CASE 355J-02, STYLE 1

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V _{CES}	65	Vdc
Collector–Base Voltage	V _{CBO}	65	Vdc
Emitter–Base Voltage	V _{EBO}	3.5	Vdc
Collector Current — Peak (1)	I _C	29	Adc
Total Device Dissipation @ T _C = 25°C (1), (2) Derate above 25°C	P _D	1460 8.3	Watts W/°C
Storage Temperature Range	T _{stg}	–65 to +200	°C
Junction Temperature	T _J	200	°C

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (3)	R _{θJC}	0.12	°C/W

NOTES:

1. Under pulse RF operating conditions.
2. These devices are designed for RF operation. The total device dissipation rating applies only when the devices are operated as pulsed RF amplifiers.
3. Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques. (Worst case θ_{JC} value measured @ 32 μ s, 2%.)

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

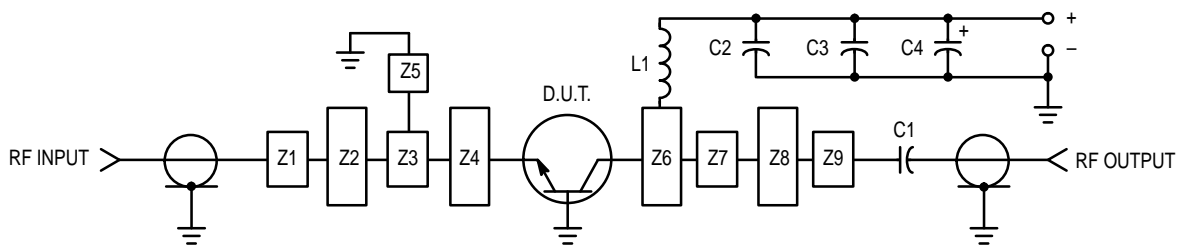
Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage ($I_C = 60 \text{ mAdc}$, $V_{BE} = 0$)	$V_{(BR)CES}$	65	—	—	Vdc
Collector–Base Breakdown Voltage ($I_C = 60 \text{ mAdc}$, $I_E = 0$)	$V_{(BR)CBO}$	65	—	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \text{ mAdc}$, $I_C = 0$)	$V_{(BR)EBO}$	3.5	—	—	Vdc
Collector Cutoff Current ($V_{CB} = 36 \text{ Vdc}$, $I_E = 0$)	I_{CBO}	—	—	25	mAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 5.0 \text{ Adc}$, $V_{CE} = 5.0 \text{ Vdc}$)	h_{FE}	20	—	—	—
--	----------	----	---	---	---

FUNCTIONAL TESTS

Common–Base Amplifier Power Gain ($V_{CC} = 50 \text{ Vdc}$, $P_{Out} = 500 \text{ W Peak}$, $f = 1090 \text{ MHz}$)	G_{PB}	8.5	9.0	—	dB
Collector Efficiency ($V_{CC} = 50 \text{ Vdc}$, $P_{Out} = 500 \text{ W Peak}$, $f = 1090 \text{ MHz}$)	η	40	45	—	%
Load Mismatch ($V_{CC} = 50 \text{ Vdc}$, $P_{Out} = 500 \text{ W Peak}$, $f = 1090 \text{ MHz}$, $VSWR = 10:1$ All Phase Angles)	ψ	No Degradation in Output Power			



- C1 — 82 pF 100 Mil Chip Capacitor
- C2 — 39 pF 100 Mil Chip Capacitor
- C3 — 0.1 μF
- C4 — 100 μF , 100 Vdc, Electrolytic
- L1 — 3 Turns #18 AWG, 1/8" ID, 0.18 Long

- Z1–Z9 — Microstrip, See Details
- Board Material — Teflon, Glass Laminate
- Dielectric Thickness = 0.030"
- $\epsilon_r = 2.55$, 2 Oz. Copper

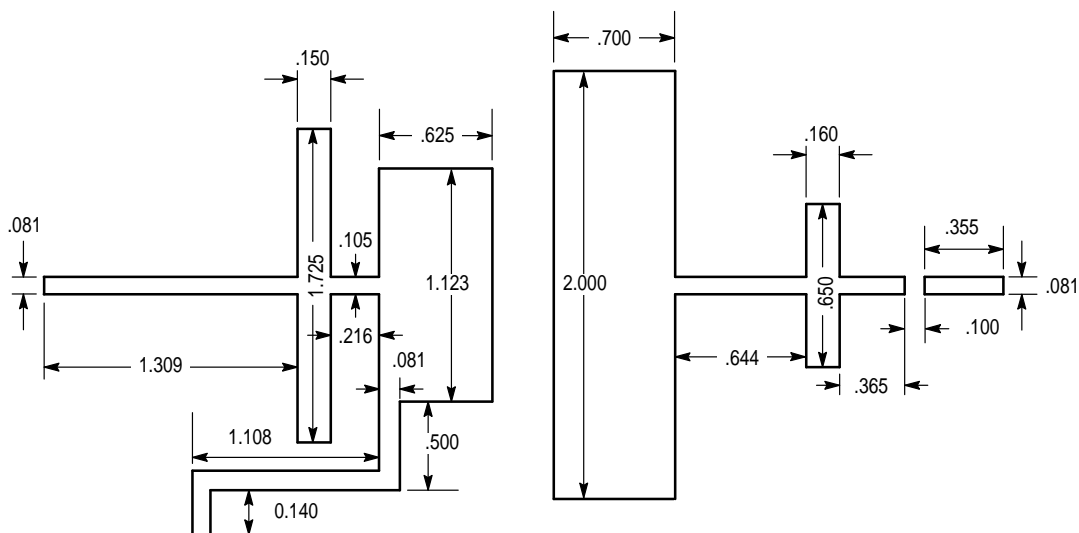


Figure 1. Test Circuit

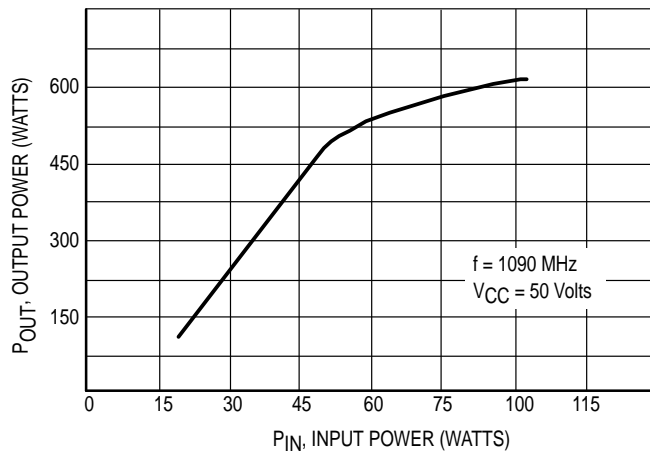
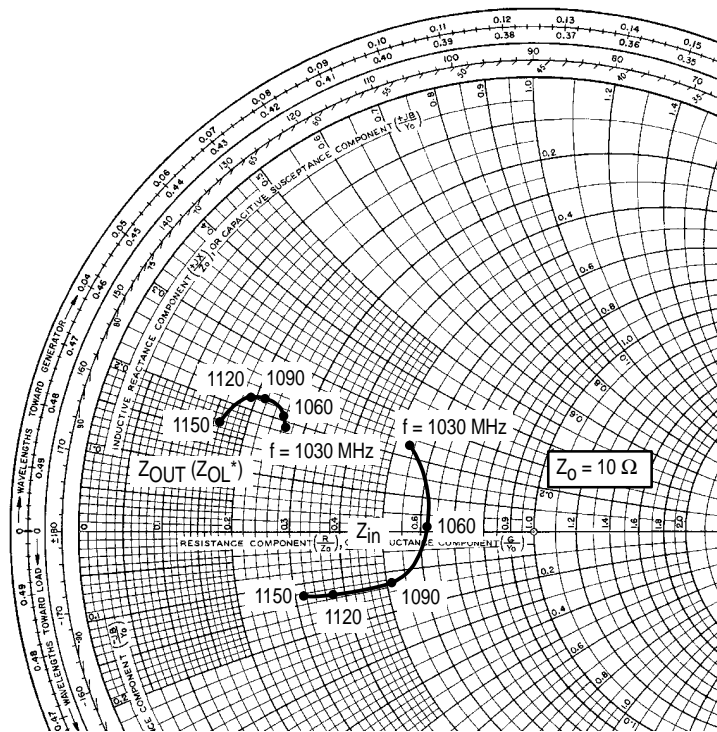


Figure 2. Output Power versus Input Power



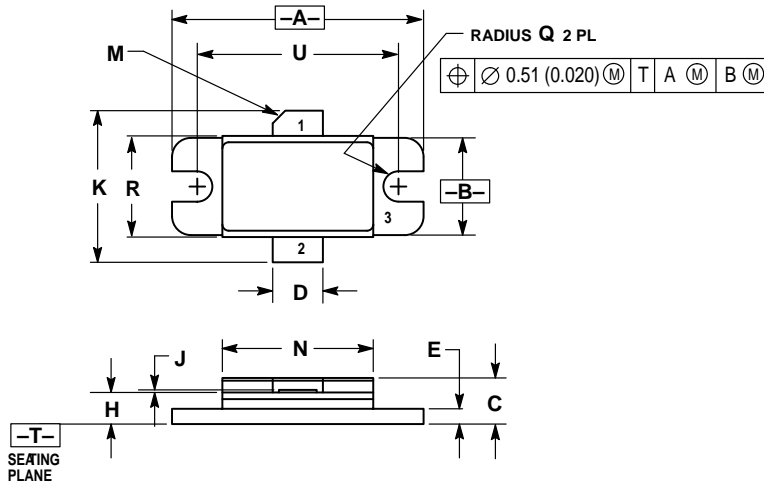
$P_{OUT} = 500 \text{ W Pk}$ $V_{CC} = 50 \text{ V}$

f MHz	Z_{in} OHMS	Z_{OL}^* (Z_{OUT}) OHMS
1030	$5.3 + j2.25$	$2.6 + j1.89$
1060	$6.2 + j0.2$	$2.56 + j2.0$
1090	$5.2 - j1.4$	$2.12 + j2.2$
1120	$3.7 - j1.35$	$1.9 + j2.15$
1150	$3.15 - j1.3$	$1.6 + j1.62$

Z_{OL}^* is the conjugate of the optimum load impedance into which the device operates at a given output power voltage and frequency.

Figure 3. Series Equivalent Input/Output Impedances

PACKAGE DIMENSIONS



**CASE 355J-02
ISSUE A**

Specifications subject to change without notice.

- **North America:** Tel. (800) 366-2266, Fax (800) 618-8883
- **Asia/Pacific:** Tel.+81-44-844-8296, Fax +81-44-844-8298
- **Europe:** Tel. +44 (1344) 869 595, Fax+44 (1344) 300 020

Visit www.macom.com for additional data sheets and product information.

Replaces MRF10500/D

tyco / Electronics

MACOM